PC923X

High Speed *OPIC Photocoupler for MOS-FET / IGBT Drive

※ Lead forming type (I type) and taping reel type (P type) are also available. (**PC923XI/PC923XP**)
※※ TÜV (VDE0884) approved type is also available as an option.

■ Features

1. Built-in direct drive circuit for MOS-FET/IGBT drive
   (I_{O1P}, I_{O2P}:0.4A)
2. High speed response (t_{PLH}, t_{PHL}:MAX.0.5μs)
3. Wide operating supply voltage range
   (V_{CC}:15 to 30V, T_a=−10 to 60˚C)
4. High noise reduction type
   (CM_H=MIN.−1.5kV/μs)
   (CM_L=MIN.1.5kV/μs)
5. Recognized by UL, file No. E64380 (Model No.**PC923**)
6. High isolation voltage between input and output
   ($V_{ISO\ (rms)}$=5.0kV)

■ Applications

1. Inverter controlled air conditioners

■ Absolute Maximum Ratings

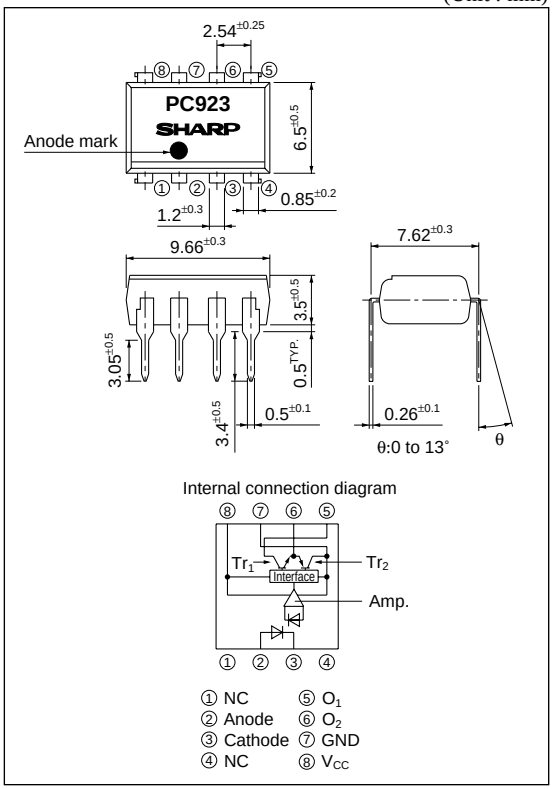
(T_a=T_{opr} unless otherwise specified)

	Parameter	Symbol	Rating	Unit
Input	Forward current	I_F	20	mA
	*1Reverse voltage	V_R	6	V
Output	Supply voltage	V_{CC}	35	V
	O_1 output current	I_1	0.1	A
	*2O_1 peak output current	I_{O1P}	0.4	A
	O_2 output current	I_{O2}	0.1	A
	*2O_2 peak output current	I_{O2P}	0.4	A
	O_1 output voltage	V_{O1}	35	V
	Power dissipation	P_O	500	mW
Total power dissipation		P_{tot}	550	mW
*3Isolation voltage		$V_{iso\ (rms)}$	5.0	kV
Operating temperature		T_{opr}	−25 to +80	˚C
Storage temperature		T_{stg}	−55 to +125	˚C
*4Soldering temperature		T_{sol}	260	˚C

*1 T_a=25˚C
*2 Pulse width≤0.15μs, Duty ratio:0.01
*3 40 to 60%RH, AC for 1minute, T_a=25˚C
*4 For 10s

■ Outline Dimensions

(Unit : mm)



* "OPIC"(Optical IC) is a trademark of the SHARP Corporation. An OPIC consists of a light-detecting element and signal-processing circuit integrated onto a single chip.

■ Electro-optical Characteristics

(T_a=T_{opr} unless otherwise specified)

	Parameter	Symbol	*5Conditions	MIN.	TYP.	MAX.	Unit
Input	Forward voltage	V_{F1}	T_a=25˚C, I_F=10mA	–	1.6	1.75	V
		V_{F2}	T_a=25˚C, I_F=0.2mA	1.2	1.5	–	V
	Reverse current	I_R	T_a=25˚C, V_R=5V	–	–	10	μA
	Terminal capacitance	C_t	T_a=25˚C, V=0, f=1kHz	–	30	250	pF
Output	Operating supply voltage	V_{CC}	T_a=–10 to 60˚C	15	–	30	V
			–	15	–	24	V
	*6 O_1 low level output voltage	V_{O1L}	V_{CC1}=12V, V_{CC2}=–12V I_{O1}=0.1A, I_F=5mA	–	0.2	0.4	V
	*7 O_2 high level output voltage	V_{O2H}	V_{CC}=V_{O1}=24V, I_{O2}=–0.1A, I_F=5mA	18	21	–	V
	*8 O_2 low level output voltage	V_{O2L}	V_{CC}=24V, I_{O2}=0.1A, I_F=0	–	1.2	2.0	V
	*9 O_1 leak current	I_{O1L}	T_a=25˚C, V_{CC}=V_{O1}=35V, I_F=0	–	–	500	μA
	*10 O_2 leak current	I_{O2L}	T_a=25˚C, V_{CC}=V_{O2}=35V, I_F=5mA	–	–	500	μA
	*11 High level supply current	I_{CCH}	T_a=25˚C, V_{CC}=24V, I_F=5mA	–	6	10	mA
			V_{CC}=24V, I_F=5mA	–	–	14	mA
	*11 Low level supply current	I_{CCL}	T_a=25˚C, V_{CC}=24V, I_F=0	–	8	13	mA
			V_{CC}=24V, I_F=0	–	–	17	mA
Transfer characteristics	*12 "Low→High" threshold input current	I_{FLH}	T_a=25˚C, V_{CC}=24V	0.3	1.5	3.0	mA
			V_{CC}=24V	0.2	–	5.0	mA
	Isolation resistance	R_{ISO}	T_a=25˚C, DC=500V, 40 to 60%RH	5×10^{10}	10^{11}	–	Ω
	Response time *13 "Low→High" propagation delay time	t_{PLH}	T_a=25˚C, V_{CC}=24V, I_F=5mA R_C=47Ω, C_G=3 000pF	–	0.3	0.5	μs
	Response time *13 "High→Low" propagation delay time	t_{PHL}		–	0.3	0.5	μs
	Response time *13 Rise time	t_r		–	0.2	0.5	μs
	Response time *13 Fall time	t_f		–	0.2	0.5	μs
	*14 Instantaneous common mode rejection voltage "Output:High level"	CM_H	T_a=25˚C, V_{CM}=600V (peak) I_F=5mA, V_{CC}=24V, ΔV_{O2H}=2.0V	–1.5	–	–	kV/μs
	*14 Instantaneous common mode rejection voltage "Output:Low level"	CM_L	T_a=25˚C, V_{CM}=600V (peak) I_F=0, V_{CC}=24V, ΔV_{O2L}=2.0V	1.5	–	–	kV/μs

*5 When measuring output and transfer characteristics, connect a by-pass capacitor (0.01μF or more) between V_{CC} and GND near the device
*6 Refer to Fig.1
*7 Refer to Fig.2
*8 Refer to Fig.3
*9 Refer to Fig.4
*10 Refer to Fig.5
*11 Refer to Fig.6
*12 I_{FLH} represents forward current when output goes from "Low" to "High", Refer to Fig.7
*13 Refer to Fig.8
*14 Refer to Fig.9

■ Truth Table

Input	O_2 Output	Tr.1	Tr.2
ON	High level	ON	OFF
OFF	Low level	OFF	ON

■ Test Circuit

Fig.1

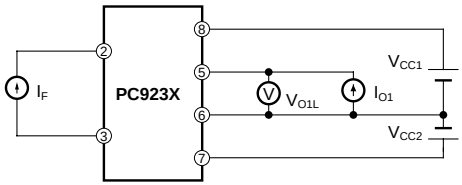


Fig.2

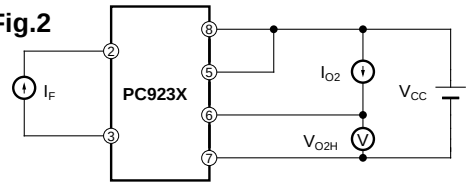
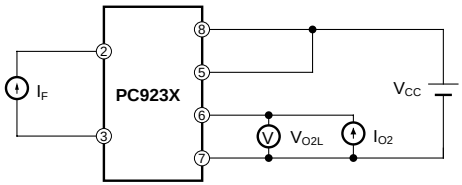


Fig.3



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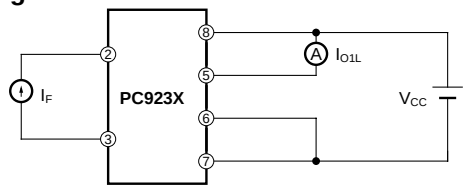


Fig.5

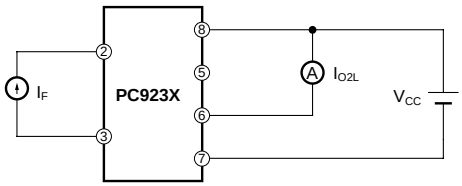


Fig.6

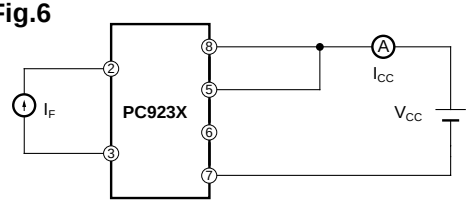


Fig.7

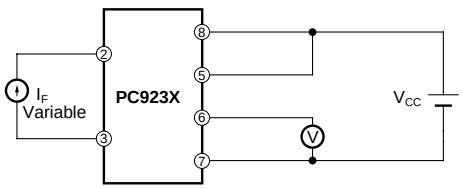


Fig.8

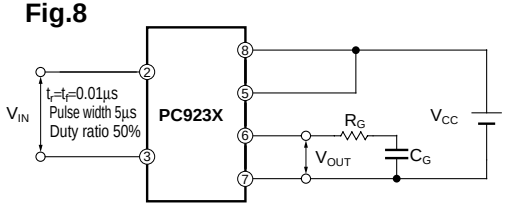
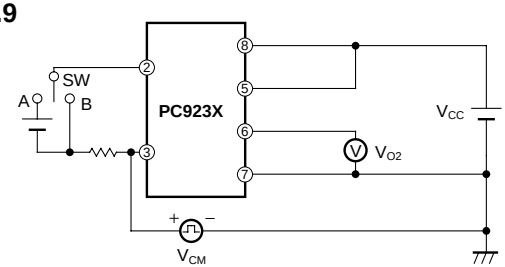
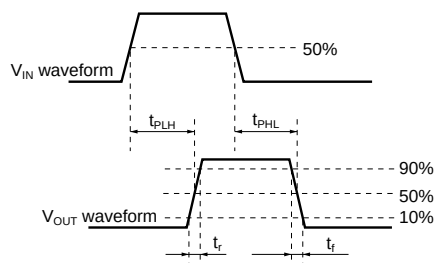


Fig.9





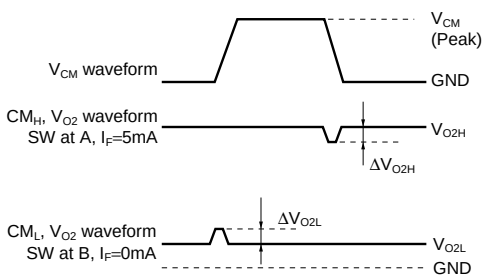


Fig.10 Forward Current vs. Ambient Temperature

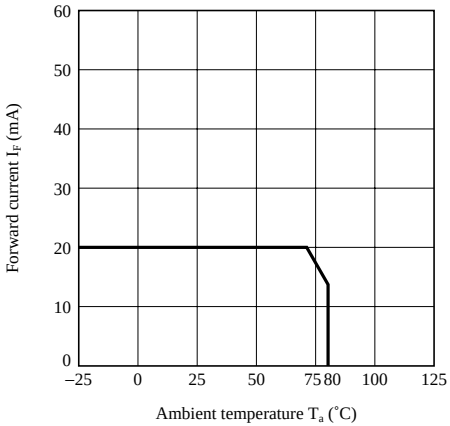


Fig.11 Power Dissipation vs. Ambient Temperature

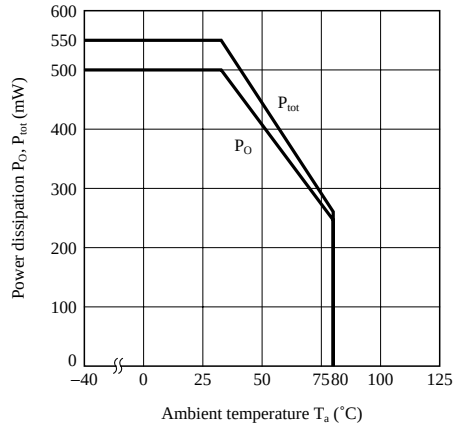


Fig.12 Forward Current vs. Forward Voltage

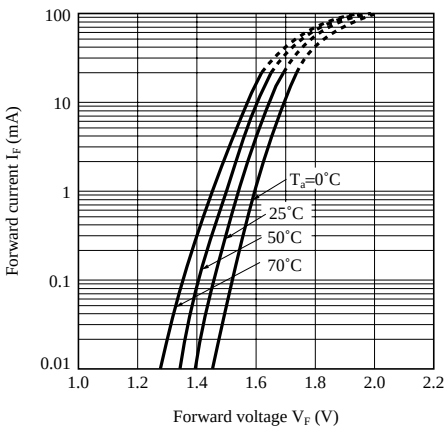


Fig.13 "Low→High" Relative Threshold Input Current vs. Supply Voltage

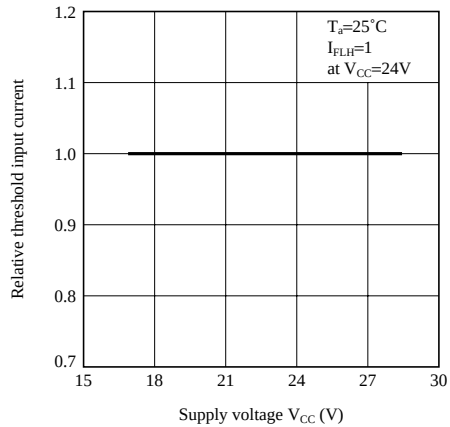


Fig.14 "Low→High" Relative Threshold Input Current vs. Ambient Temperature

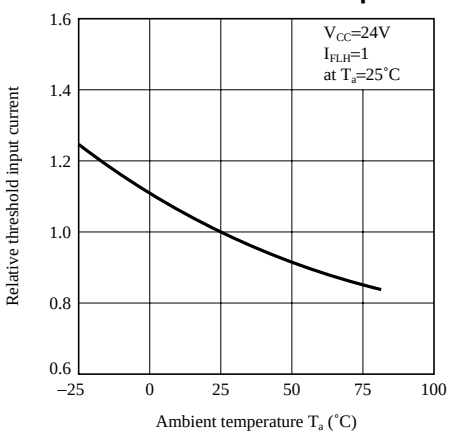


Fig.15 O_1 Low Level Output Voltage vs. O_1 Output Current

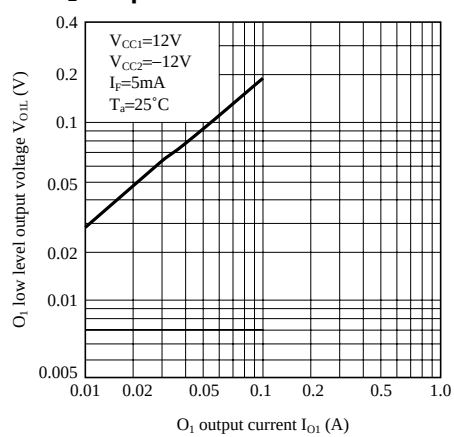


Fig.16 O_1 Low Level Output Voltage vs. Ambient Temperature

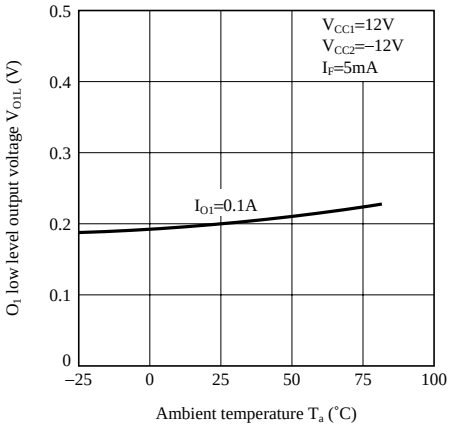


Fig.17 O_2 High Level Output Voltage vs. Supply Voltage

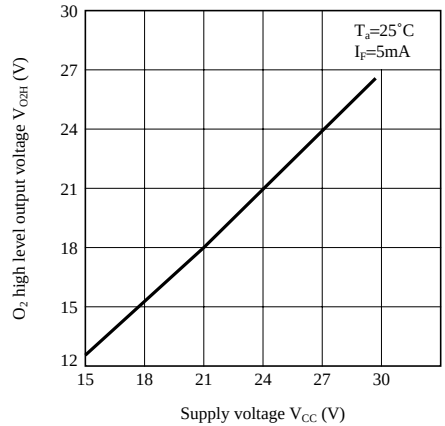


Fig.18 O_2 High Level Output Voltage vs. Ambient Temperature

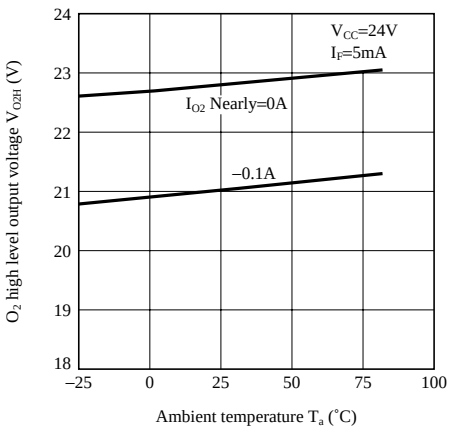


Fig.19 O_2 Low Level Output Voltage vs. O_2 Output Current

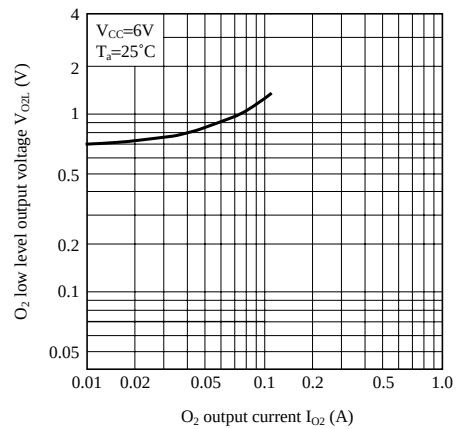


Fig.20 O_2 Low Level Output Voltage vs. Ambient Temperature

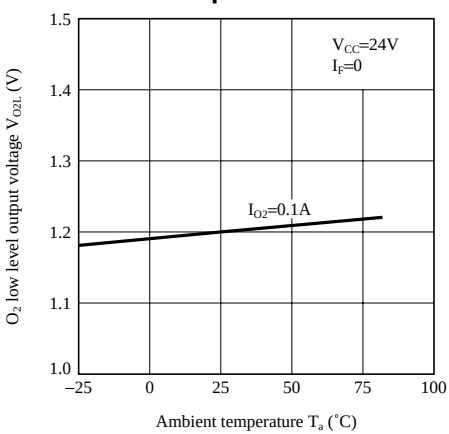


Fig.21 High Level Supply Current vs. Supply Voltage

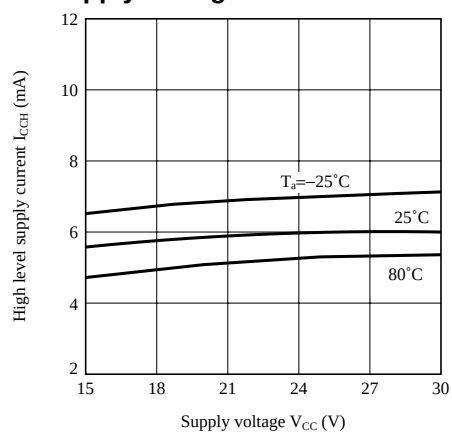


Fig.22 Low Level Supply Current vs. Supply Voltage

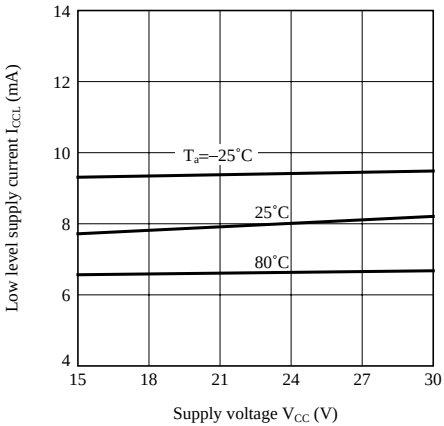


Fig.23 Propagation Delay Time vs. Forward Current

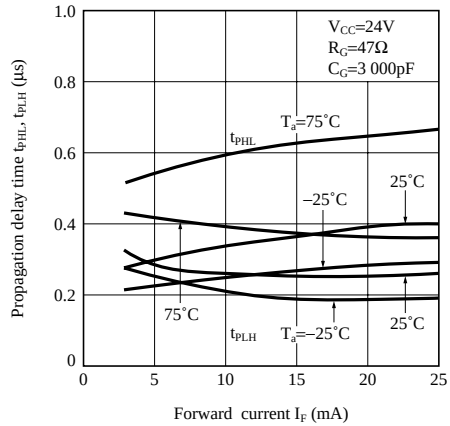
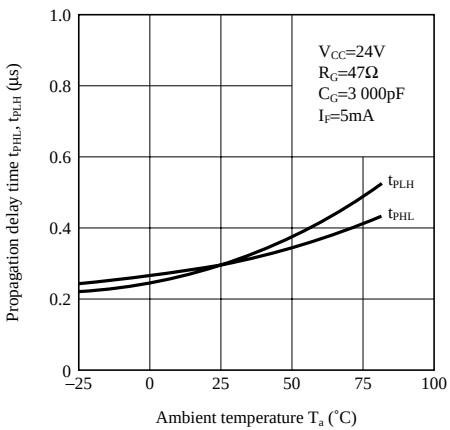
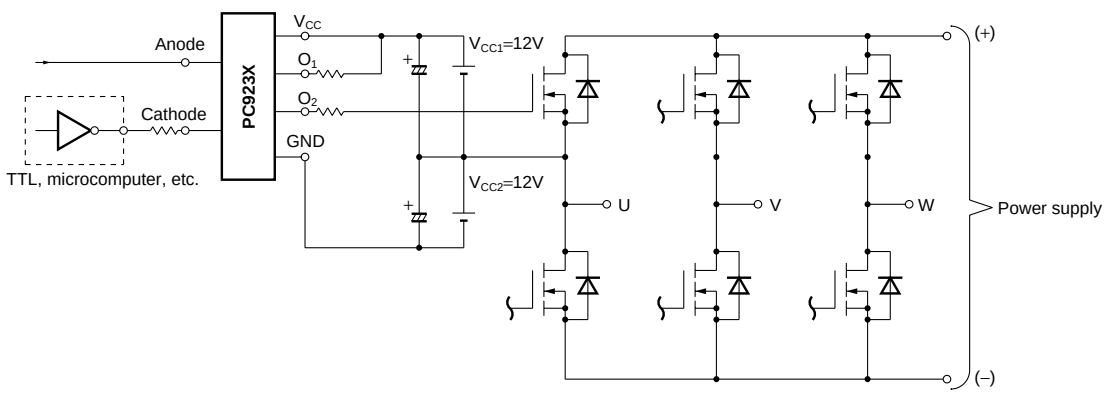


Fig.24 Propagation Delay Time vs. Ambient Temperature



■ Application Circuit (Foe Power MOS-FET Driving Inverter)



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  --- Telecommunication equipment [terminal]
  --- Test and measurement equipment
  --- Industrial control
  --- Audio visual equipment
  --- Consumer electronics

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  --- Traffic signals
  --- Gas leakage sensor breakers
  --- Alarm equipment
  --- Various safety devices, etc.

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